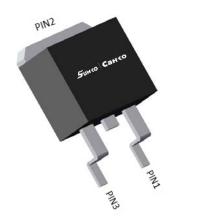


PIN₂

MBRBL20200CT

Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260°C

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-263

Molding compound meets UL 94 V-0 flammability rating -

• Terminals: Tin plated leads, solderable per

J-STD-002 and JESD22-B102

• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

PIN1

PIN3

PARAMETER	SYMBOL	UNIT	MBRBL20200CT
Device marking code			MBRBL20200CT
Repetitive Peak Reverse Voltage	V_{RRM}	V	200
Average Rectified Output Current @60Hz sine wave, R-load, Ta (FIG 1)	Io	А	20
Surge(Non-repetitive)Forward Current @60Hz half sine-wave, 1 cycle, Ta=25℃	I _{FSM}	А	160
Current Squared Time @1ms≤t≤8.3ms Tj=25˚ℂ,rating of per diode	l ² t	A ² s	106
Storage Temperature	T _{stg}	°C	-55 ~ +150
Junction Temperature	Tj	$^{\circ}$	-55 ~ +150

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL20200CT
Maximum instantaneous forward voltage drop per diode	V_{FM}	V	I _{FM} =10.0A	0.88
Maximum DC reverse current at rated DC blocking voltage per diode	I _{RRM1}	mA	V _{RM} =V _{RRM} Ta=25°C	0.1
	I _{RRM2}		V _{RM} =V _{RRM} Ta=100°C	20

■Thermal Characteristics (T_a=25°C Unless otherwise specified)

F	PARAMETER	SYMBOL	UNIT	MBRBL20200CT
Thermal Resistance	Between junction and case	$R_{ heta J ext{-}C}$	%\W	2.0



MBRBL20200CT

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBRBL20200CT	Approximate 1.43	50	2000	8000	Tube
MBRBL20200CT	Approximate 1.43	1000	2000	10000	Reel

■Characteristics (Typical)

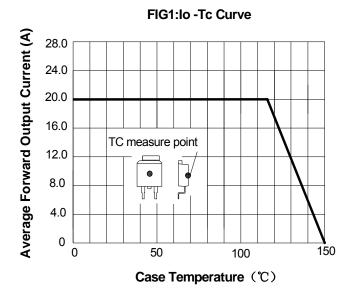
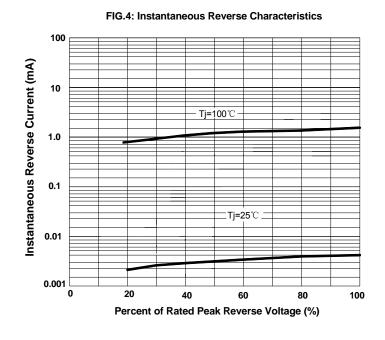


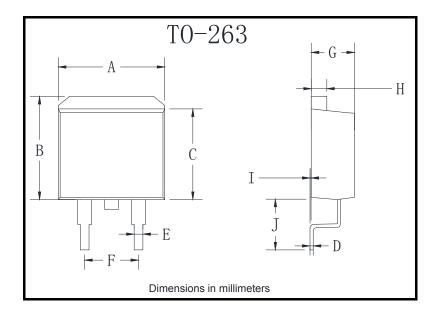
FIG2:Surge Forward Current Capability 240 Peak Forward Surge Current (A) 200 160 8.3ms Single Half Sine-Wave 120 JEDEC Method 80 40 0 2 5 50 100 **Number of Cycles**





MBRBL20200CT

■Outline Dimensions



TO-263					
Dim	Min	Max			
Α	9.5	11.5			
В	9.7	10.5			
С	8.4	9.0			
D	0.28	0.64			
E	0.68	0.94			
F	4.55	5.6			
G	4.04	5.10			
Н	1.14	1.4			
I	0	0.2			
J	4.9	6.05			



MBRBL20200CT

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